Product data sheet

1. General description

Hyperfast power diode in a SOD113A (2-lead TO-220-F) plastic package.

2. Features and benefits

- Fast switching
- Isolated plastic package
- Low leakage current
- · Low reverse recovery current
- Low thermal resistance
- · Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Active PFC in air conditioner
- High frequency switched-mode power supplies
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Va	lues		Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			6	00		V
I _{F(AV)}	average forward current	δ = 0.5 ; square-wave pulse; $T_h \le 61$ °C; Fig. 1; Fig. 2		10			А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μs; T_h ≤ 61 °C; square-wave pulse	20			А	
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4				А	
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse				Α	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 4</u>		-	2.5	3.2	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 4</u>		-	1.3	2	V
Dynamic	characteristics				,		
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 5$		-	12	18	ns
		$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 5$		-	19	-	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	
2	А	anode		K — A
mb	n.c.	mounting base; isolated		001aaa020

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYC10X-600P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113A

7. Marking

Table 4. Marking codes

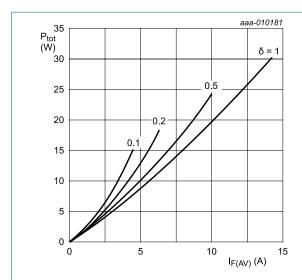
Type number	Marking codes
BYC10X-600P	BYC10X-600P

8. Limiting values

Table 5. Limiting values

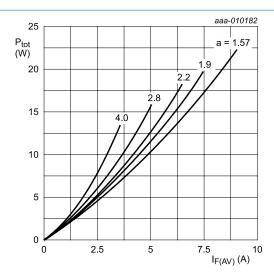
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	DC	600	V
I _{F(AV)}	average forward current	$δ = 0.5$; square-wave pulse; $T_h \le 61$ °C; Fig. 1; Fig. 2; Fig. 3	10	Α
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_h \le 61 °C$; square-wave pulse	20	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	150	Α
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	165	Α
T _{stg}	storage temperature		-65 to 175	°C
T _j	junction temperature		175	°C



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$ $V_o = 1.572 \text{ V; } R_s = 0.040 \Omega$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 1.572 V; R_s = 0.040 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

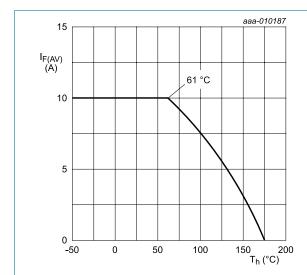


Fig. 3. Forward current as a function of heatsink temperature; maximum values

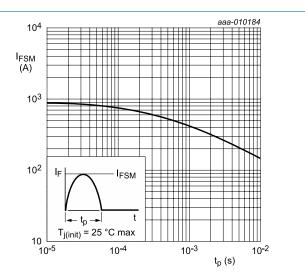


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; Fig 5	-	-	4.8	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W

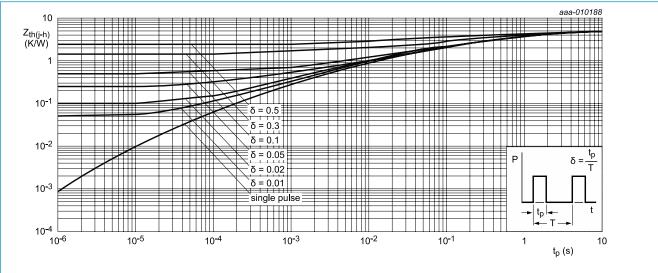


Fig. 5. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

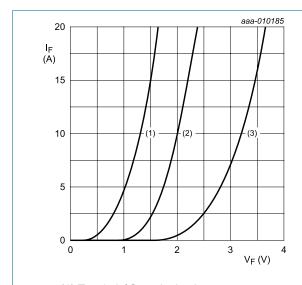
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink; f = 1 MHz	-	10	-	PF

11. Characteristics

Table 8 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 6</u>	-	2.5	3.2	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.3	2	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 600 V; T _j = 150 °C	-	-	0.8	mA
Dynamic	characteristics			'		
Q_r	recovered charge	$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_J = 25 \text{ °C}; Fig. 7$	-	26	-	nC
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 ^{\circ}\text{C}; Fig. 7$	-	83	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	12	18	ns
		$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	19	-	ns
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	26	-	ns
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	34	-	
I _{RM}	peak reverse recovery current	$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	2	-	А
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_i = 125 \text{ °C}; Fig. 7$	-	4.8	-	А



(1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values

(3) $T_j = 25$ °C; maximum values $V_0 = 1.572$ V; $R_s = 0.040$ Ω



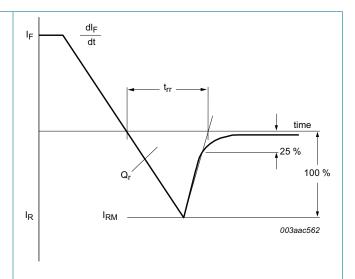
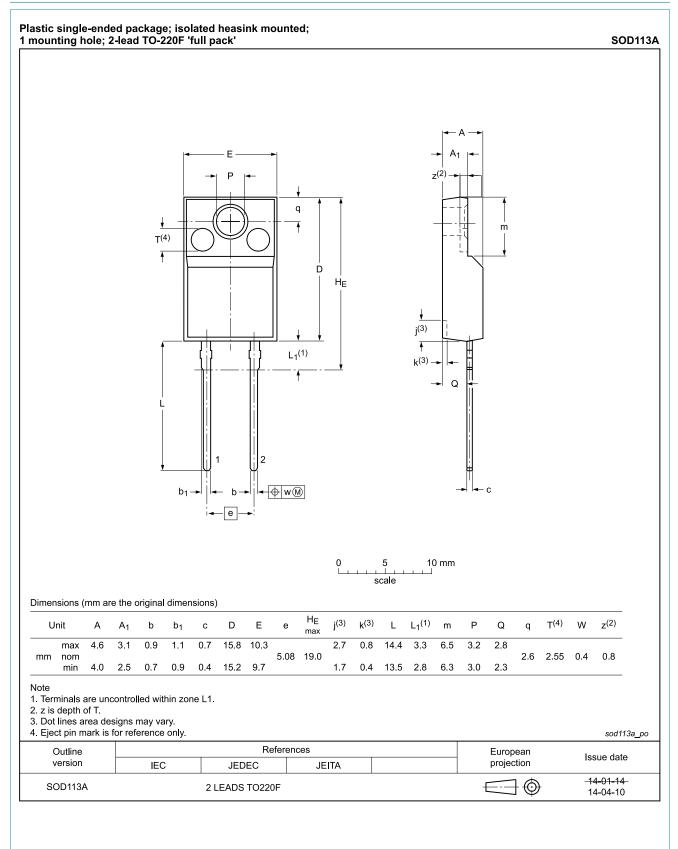


Fig. 7. Reverse recovery definitions; ramp recovery

12. Package outline



13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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